

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("20040188741").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/24 08:38
L2	48707	harada.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/24 08:56
L3	177	2 and hirofumi	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/24 08:56
L4	12	("5016067" "5034785" "5160491" "5508534" "5918114" "5945723" "6069043" "6177734" "6211549" "6274905" "6323518" "6461918").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/24 09:34
L5	3	("4503449" "5877527" "6452228").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/24 09:48
L6	4	("4992390" "5473176" "5578522" "6198127").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/24 09:57
L7	2	("6,639,275").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/24 09:57
L8	780	(257/329).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/24 11:03
L9	1288	(257/330).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/24 12:46
L10	425	(257/332).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/24 10:05
L11	5	("20020195655" "5408116" "6117734" "6482701" "6693011").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/24 10:41
L12	2	("6278155" "6307755").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/24 12:10

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L13	0	("6781195").URPN.	USPAT	OR	ON	2006/04/24 12:10
L14	13	(vertical adj mos adj transistor) and epitaxial and ((body adj region) with (source and (body adj contact))) and (trench or groove)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/24 13:19
L15	2	("6020600").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/24 13:18
L16	12	(vertical adj mos adj transistor) and epitaxial and ((body adj region) with (source and (body adj contact))) and (trench or groove)	US-PGPUB; USPAT	OR	ON	2006/04/24 13:25
L17	1	(vertical adj mos adj transistor) and epitaxial and ((body adj region) with (source and (body adj contact))) and (trench or groove) and (gate adj insulat\$3) and (doped adj polycrystalline adj silicon) and insulator and metallic	US-PGPUB; USPAT	OR	ON	2006/04/24 13:28
L18	1	(vertical adj mos adj transistor) and epitaxial and ((body adj region) with (source and (body adj contact))) and (trench or groove) and (gate adj insulat\$3) and (doped adj polycrystalline adj silicon) and insulator and metallic	US-PGPUB	OR	ON	2006/04/24 13:28